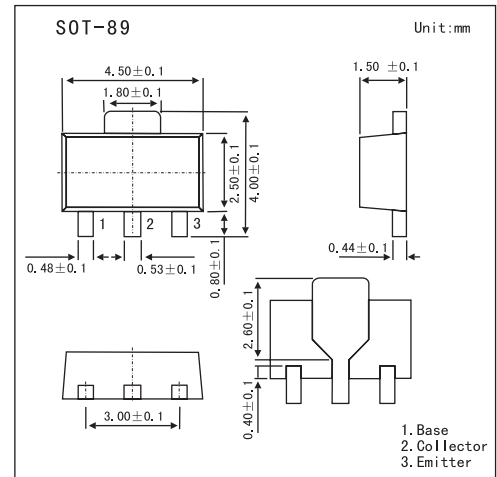


## PNP Switching Transistor

## PXT2907A

## ■ Features

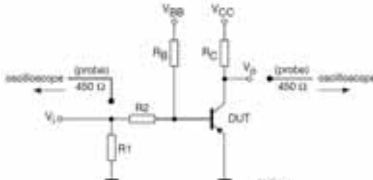
- High current (max. 600 mA)
- Low voltage (max. 60 V).

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-60	V
Collector-emitter voltage	$V_{CE0}$	-60	V
Emitter-base voltage	$V_{EB0}$	-5	V
Collector current	$I_C$	-600	mA
Peak collector current	$I_{CM}$	-800	mA
Peak base current	$I_{BM}$	-200	mA
Total power dissipation	$P_{tot}$	1.3	W
Storage temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Junction temperature	$T_j$	150	$^\circ\text{C}$
Operating ambient temperature	$R_{amb}$	-65 to +150	$^\circ\text{C}$
Thermal resistance from junction to ambient	$R_{th(j-a)}$	97	K/W
Thermal resistance from junction to soldering point	$R_{th(j-s)}$	17	K/W

## PXT2907A

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Collector cutoff current	ICBO	IE = 0; VCB = -50 V			-10	nA	
		IE = 0; VCB = -50 V; Tj = 125 °C			-10	μA	
Emitter cutoff current	IEBO	IC = 0; VEB = -5 V			-50	nA	
DC current gain	hFE	IC = -0.1 mA; VCE = -1 V	75				
		IC = -1 mA; VCE = -1 V	100				
		IC = -10 mA; VCE = -1 V	100				
		VCE = -2 V, IC = -150 mA	100		300		
		IC = -500 mA; VCE = -2 V	50				
collector-emitter saturation voltage	VCEsat	IC = -150 mA; IB = -15 mA			-400	mV	
		IC = -500 mA; IB = -50 mA			-1.6	V	
base-emitter saturation voltage	VBEsat	IC = -150 mA; IB = -15 mA			-1.3	V	
		IC = -500 mA; IB = -50 mA			-2.6	V	
Collector capacitance	Cc	IE = iE = 0; VCB = -10 V; f = 1 MHz			8	pF	
Emitter capacitance	Ce	IC = ic = 0; VEB = -500 mV; f = 1 MHz			35	pF	
Transition frequency	fr	IC = -20 mA; VCE = -10 V; f = 100 MHz	200			MHz	
Turn-on time	ton	ICon = -150 mA; IBon = -15 mA; IBoff = 15 mA			40	ns	
Delay time	td				12	ns	
Rise time	tr					30	ns
Turn-off time	toff					365	ns
Storage time	ts					300	ns
Fall time	tf					65	ns

## ■ Marking

Marking	p2F
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